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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	LINbus, SCI
Peripherals	LVD, POR, PWM
Number of I/O	14
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 10x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	16-TSSOP
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08se8ctgr

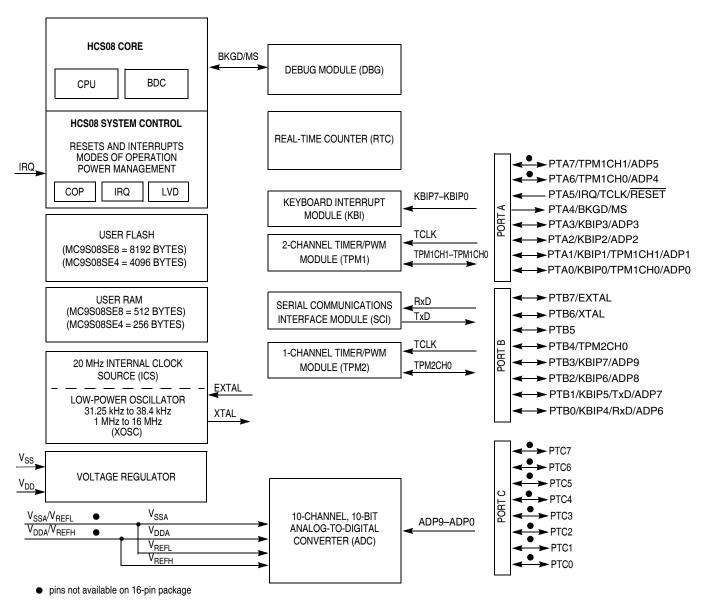
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1 MCU Block Diagram

The block diagram, Figure 1, shows the structure of the MC9S08SE8 series MCUs.



Notes:

When PTA4 is configured as BKGD, pin is bi-directional.

For the 16-pin package: V_{SSA}/V_{REFL} and V_{DDA}/V_{REFH} are double bonded to V_{SS} and V_{DD} respectively.

Figure 1. MC9S08SE8 Series Block Diagram



Pin Assignments

2 Pin Assignments

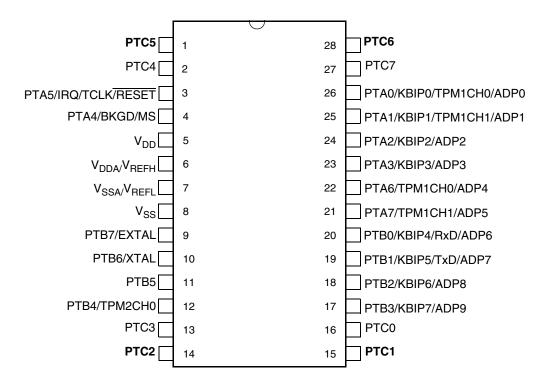
This chapter shows the pin assignments in the packages available for the MC9S08SE8 series.

Table 1. Pin Availability by Package Pin-Count

Pin Nu (Packa		<	- Lowest Pri	iority> Hig	hest
28 (SOIC/PDIP)	16 (TSSOP)	Port Pin	Alt 1	Alt 2	Alt 3
1	_	PTC5			
2	_	PTC4			
3	1	PTA5	IRQ	TCLK	RESET
4	2	PTA4		BKGD	MS
5	3				V_{DD}
6	_			V _{DDA}	V _{REFH}
7	_			V _{SSA}	V _{REFL}
8	4				V _{SS}
9	5	PTB7	EXTAL		
10	6	PTB6	XTAL		
11	7	PTB5			
12	8	PTB4		TPM2CH0	
13	_	PTC3			
14	_	PTC2			
15	_	PTC1			
16	_	PTC0			
17	9	PTB3	KBIP7		ADP9
18	10	PTB2	KBIP6		ADP8
19	11	PTB1	KBIP5	TxD	ADP7
20	12	PTB0	KBIP4	RxD	ADP6
21	_	PTA7		TPM1CH1 ¹	ADP5
22	_	PTA6		TPM1CH0 ¹	ADP4
23	13	PTA3	KBIP3		ADP3
24	14	PTA2	KBIP2		ADP2
25	15	PTA1	KBIP1	TPM1CH1 ¹	ADP1
26	16	PTA0	KBIP0	TPM1CH0 ¹	ADP0
27	_	PTC7			
28	_	PTC6			

¹ TPM1 pins can be remapped to PTA7, PTA6 and PTA1,PTA0





Pins in **bold** are lost in the next lower pin count package.

Figure 2. MC9S08SE8 Series in 28-Pin PDIP/SOIC Package

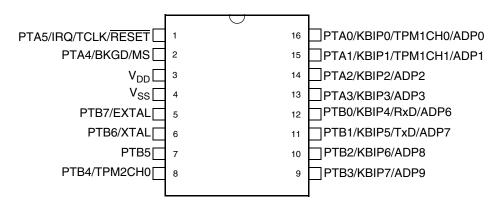


Figure 3. MC9S08SE8 in 16-Pin TSSOP Package



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Electrical Characteristics

3 Electrical Characteristics

This chapter contains electrical and timing specifications.

3.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 2. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

3.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

MC9S08SE8 Series MCU Data Sheet, Rev. 4



Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	-0.3 to 5.8	V
Maximum current into V _{DD}	I _{DD}	120	mA
Digital input voltage	V _{In}	-0.3 to $V_{DD} + 0.3$	V
Instantaneous maximum current Single pin limit (applies to all port pins) ^{1, 2, 3}	I _D	±25	mA
Storage temperature range	T _{stg}	-55 to 150	°C

Table 3. Absolute Maximum Ratings

3.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Rating		Symbol	Value	Unit	
Operating temperature range (T _A	T _L to T _H -40 to 85 -40 to 105 -40 to 125	°C		
Maximum junction temperature	T_JM	135	°C		
	28-pin SOIC		70		
Thermal resistance single-layer board	28-pin PDIP		68	°C/W	
	16-pin TSSOP	Δ	129		
	28-pin SOIC	$\theta_{\sf JA}$	48		
Thermal resistance four-layer board	28-pin PDIP		49	°C/W	
	16-pin TSSOP		85		

Table 4. Thermal Characteristics

Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

 $^{^{2}\,}$ All functional non-supply pins are internally clamped to $\rm V_{SS}$ and $\rm V_{DD}.$

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).



Table 5. ESD and Latch-up Test Conditions (continued)

Model	Description	Symbol	Value	Unit
Latch-up	Minimum input voltage limit	_	-2.5	٧
Laterrup	Maximum input voltage limit	_	7.5	V

Table 6. ESD and Latch-up Protection Characteristics

No.	Rating ¹	Symbol	Min	Max	Unit
1	Human body model (HBM)	V _{HBM}	±2000	_	V
2	Machine model (MM)	V _{MM}	±200	_	V
3	Charge device model (CDM)	V _{CDM}	±500	_	٧
4	Latch-up current at T _A = 125 °C	I _{LAT}	±100	_	mA

¹ Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.5 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 7. DC Characteristics

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	_	Operating voltage	_	2.7		5.5	V
2	Р	Output high voltage — Low drive (PTxDSn = 0) $ 5 \text{ V, } I_{Load} = -2 \text{ mA} $ $ 3 \text{ V, } I_{Load} = -0.6 \text{ mA} $ $ 5 \text{ V, } I_{Load} = -0.4 \text{ mA} $ $ 3 \text{ V, } I_{Load} = -0.24 \text{ mA} $ $ 3 \text{ V, } I_{Load} = -0.24 \text{ mA} $ $ 0 \text{ Output high voltage} \text{ — High drive (PTxDSn = 1)} $ $ 5 \text{ V, } I_{Load} = -10 \text{ mA} $ $ 3 \text{ V, } I_{Load} = -3 \text{ mA} $ $ 5 \text{ V, } I_{Load} = -2 \text{ mA} $. V _{OH}	$V_{DD} - 1.5$ $V_{DD} - 1.5$ $V_{DD} - 0.8$ $V_{DD} - 0.8$ $V_{DD} - 1.5$ $V_{DD} - 1.5$ $V_{DD} - 1.5$ $V_{DD} - 0.8$			V
		3 V, I _{Load} = -0.4 mA Output low voltage — Low drive (PTxDSn = 0)		V _{DD} - 0.8		_	
		5 V, I _{Load} = 2 mA 3 V, I _{Load} = 0.6 mA 5 V, I _{Load} = 0.4 mA 3 V, I _{Load} = 0.24 mA	V	1.5 1.5 0.8 0.8		_ _ _	V
3	Р	Output low voltage — High drive (PTxDSn = 1) 5 V, I _{Load} = 10 mA 3 V, I _{Load} = 3 mA 5 V, I _{Load} = 2 mA 3 V, I _{Load} = 0.4 mA	. V _{OL}	1.5 1.5 0.8 0.8		_ _ _ _	V
4	Р	Output high current — Max total I _{OH} for all ports 5 V 3 V	I _{OHT}		_ _	100 60	mA



Table 7. DC Characteristics (continued)

Num	С	Parameter		Min	Typical ¹	Max	Unit
5	Р	Output low current — Max total I _{OL} for all ports 5 V 3 V	I _{OLT}		_	100 60	mA
6	Р	Input high voltage; all digital inputs	V _{IH}	$0.65 \times V_{DD}$	_	_	V
7	Р	Input low voltage; all digital inputs	V_{IL}	_		$0.35 \times V_{DD}$	\ \
8	Р	Input hysteresis; all digital inputs	V _{hys}	$0.06 \times V_{DD}$	_	_	mV
9	С	Input leakage current; input only pins ²	II _{In} I	_	0.1	1	μΑ
10	Р	High impedance (off-state) leakage current ²	ll _{OZ} l	_	0.1	1	μΑ
11	С	Total leakage combined for all inputs and Hi-Z pins — All input only and I/O ²	II _{OZTOT} I	_	_	2	μА
12	Р	Internal pullup resistors ³	R _{PU}	20	45	65	kΩ
13	Р	Internal pulldown resistors ⁴	R_{PD}	20	45	65	kΩ
14	D	DC injection current ^{5, 6, 7} V _{IN} < V _{SS} , V _{IN} > V _{DD} Single pin limit Total MCU limit, includes sum of all stressed pins	I _{IC}	-0.2 -5	_ _	0.2 5	mA
15	С	Input capacitance; all non-supply pins	C _{In}	_	_	8	pF
16	С	RAM retention voltage	V_{RAM}	0.6	1.0	_	V
17	Р	POR re-arm voltage ⁸	V_{POR}	0.9	1.4	2.0	V
18	D	POR re-arm time	t _{POR}	10	_	_	μs
19	Р	Low-voltage detection threshold — high range ${\rm V_{DD}} \ {\rm falling} \\ {\rm V_{DD}} \ {\rm rising}$	V _{LVD1}	3.9 4.0	4.0 4.1	4.1 4.2	V
20	Р	Low-voltage detection threshold — low range ${\rm V_{DD}\ falling} \\ {\rm V_{DD}\ falling}$	V _{LVD0}	2.48 2.54	2.56 2.62	2.64 2.70	V
21	С	Low-voltage warning threshold — high range 1 V_{DD} falling V_{DD} rising	V _{LVW3}	4.5 4.6	4.6 4.7	4.7 4.8	V
22	Р	Low-voltage warning threshold — high range 0 V _{DD} falling V _{DD} rising	V _{LVW2}	4.2 4.3	4.3 4.4	4.4 4.5	V
23	Р	Low-voltage warning threshold low range 1 \$V_{DD}\$ falling \$V_{DD}\$ rising	V _{LVW1}	2.84 2.90	2.92 2.98	3.00 3.06	V
24	С	Low-voltage warning threshold — low range 0 $V_{DD} \ \text{falling} \\ V_{DD} \ \text{rising}$	V _{LVW0}	2.66 2.72	2.74 2.80	2.82 2.88	V

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Table 7. DC Characteristics (continued)

Num	С	Parameter		Symbol	Min	Typical ¹	Max	Unit
05	+	Low-voltage inhibit reset/recover hysteresis	<i>5</i> \/	V		100		m\/
25			5 V 3 V	V_{hys}	_	100 60	_	mV
26	Р	Bandgap voltage reference ⁹		V_{BG}	1.18	1.20	1.21	V

- Typical values are measured at 25 °C. Characterized, not tested.
- ² Measured with $V_{In} = V_{DD}$ or V_{SS} .
- ³ Measured with V_{In} = V_{SS}.
- ⁴ Measured with $V_{In} = V_{DD}$.
- All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.
- ⁶ Input must be current-limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
- Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD} , the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).
- ⁸ Maximum is highest voltage that POR is guaranteed.
- 9 Factory trimmed at $V_{DD} = 5.0 \text{ V}$, Temp = 25 $^{\circ}$ C.



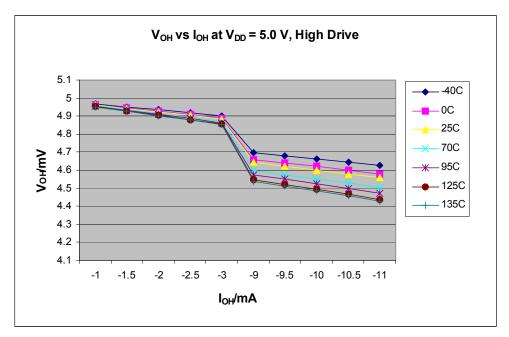


Figure 8. Typical V_{OH} vs. I_{OH} for High Drive Enabled Pad (V_{DD} = 5 V)

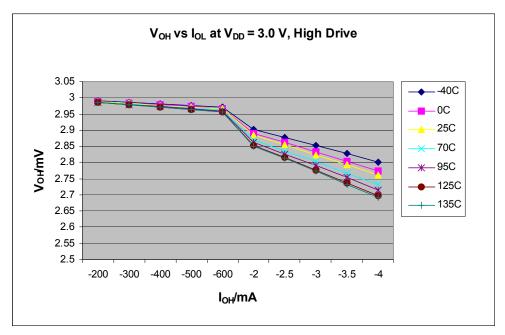


Figure 9. Typical V_{OH} vs. I_{OH} for High Drive Enabled Pad (V_{DD} = 3 V)

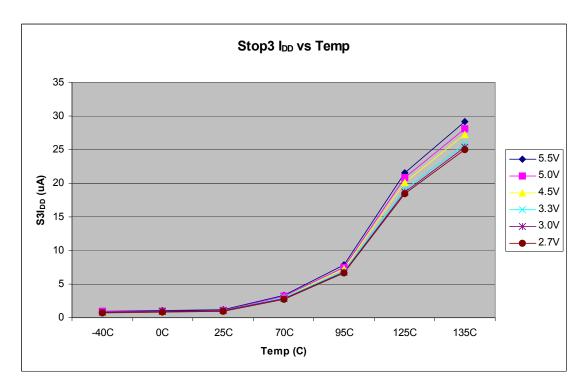


Figure 14. Typical Stop3 I_{DD} Curves

3.7 External Oscillator (XOSC) Characteristics

Table 9. Oscillator electrical specifications (Temperature Range = −40 to 125°C Ambient)

Num	С	Characteristic	Symbol	Min.	Typical ¹	Max.	Unit
1	С	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1), high gain (HGO = 1) ² High range (RANGE = 1), low power (HGO = 0) ²	f _{lo} f _{hi-hgo} f _{hi-lp}	32 1 1		38.4 16 8	kHz MHz MHz
2		Load capacitors			crystal or turer's rec		
3	_	Feedback resistor Low range (32 kHz to 100 kHz) High range (1 MHz to 16 MHz)	R _F		10 1	_ _	МΩ
4	_	Series resistor Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0)	- R _S	_ _ _	0 100 0	_ _ _	kΩ
4		High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	1 115	_ _ _	0 0 0	0 10 20	, V75



Table 9. Oscillator electrical specifications (Te	emperature Range = -40 to 125°C Ambient)
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Num	С	Characteristic	Symbol	Min.	Typical ¹	Max.	Unit
5	Т	Crystal start-up time ³ Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0) ⁴ High range, high gain (RANGE = 1, HGO = 1) ⁴	CSTL-LP CSTH-HGO CSTH-LP CSTH-HGO	_	200 400 5 15	_ _ _ _	ms
6	Т	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE or FBE mode FBELP mode	f _{extal}	0.03125 0	_	20 20	MHz MHz

¹ Typical column was characterized at 5.0 V, 25 °C or is recommended value.

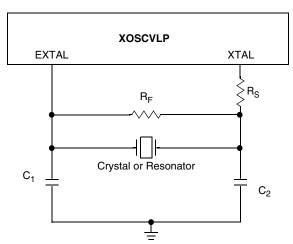


Figure 15. Typical Crystal or Resonator Circuit: High Range and Low Range/High Gain

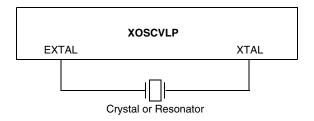


Figure 16. Typical Crystal or Resonator Circuit: Low Range/Low Power

 $^{^{2}}$ The input clock source must be divided using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications. This data will vary based upon the crystal manufacturer and board design. The crystal should be characterized by the crystal manufacturer.

⁴ 4 MHz crystal.



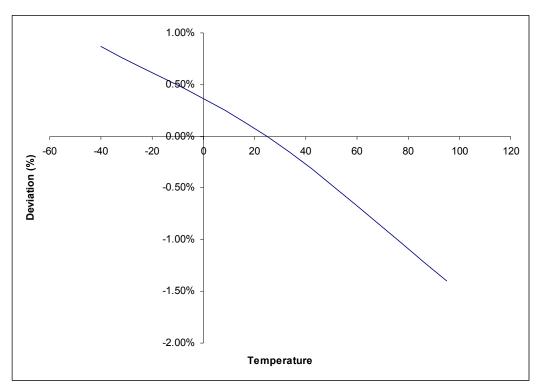


Figure 17. Deviation of DCO Output from Trimmed Frequency (20 MHz, 3.0 V)

3.9 ADC Characteristics

Table 11. 10-Bit ADC Operating Conditions

Characteristic	eristic Conditions		Min	Typ ¹	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	2.7	_	5.5	V	
Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA}) ²	ΔV_{DDA}	-100	0	100	mV	
Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA}) ²	ΔV _{SSA}	-100	0	100	mV	
Input voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	
Input capacitance		C _{ADIN}	_	4.5	5.5	pF	
Input resistance		R _{ADIN}	_	3	5	kΩ	
Analog source resistance	10-bit mode f _{ADCK} > 4MHz f _{ADCK} < 4MHz	R _{AS}			5 10	kΩ	External to MCU
	8-bit mode (all valid f _{ADCK})		_	_	10		
ADC conversion	High speed (ADLPC = 0)	f _{ADCK}	0.4	_	8.0	MHz	
clock frequency	Low power (ADLPC = 1)	ADCK	0.4	_	4.0	1411 12	

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- $^{1}~$ Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- ² DC potential difference.

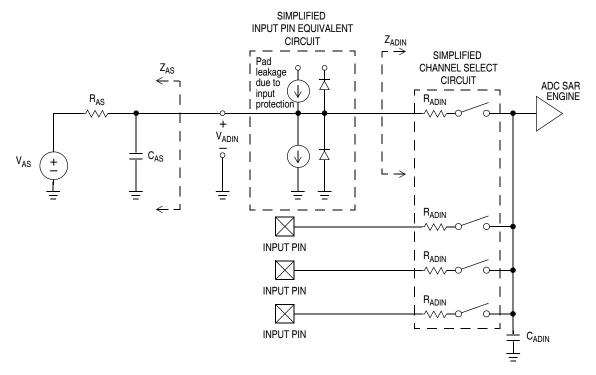


Figure 18. ADC Input Impedance Equivalency Diagram

Table 12. 10-Bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Characteristic	Conditions	С	Symb	Min	Typ ¹	Max	Unit	Comment
Supply Current ADLPC = 1 ADLSMP = 1 ADCO = 1		Т	I _{DDA}		133		μΑ	
Supply Current ADLPC = 1 ADLSMP = 0 ADCO = 1		Т	I _{DDA}		218		μΑ	
Supply Current ADLPC = 0 ADLSMP = 1 ADCO = 1		Т	I _{DDA}	_	327	_	μΑ	
Supply Current ADLPC = 0 ADLSMP = 0 ADCO = 1		D	I _{DDA}	_	0.582	1	mA	
Supply Current	Stop, Reset, Module Off	D	I _{DDA}	_	0.011	1	μΑ	

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Table 12. 10-Bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Characteristic	Conditions	С	Symb	Min	Typ ¹	Max	Unit	Comment
ADC	High Speed (ADLPC = 0)	1		2	3.3	5		t _{ADACK} =
Asynchronous Clock Source	Low Power (ADLPC = 1)	D	f _{ADACK}	1.25	2	3.3	MHz	1/f _{ADACK}
Conversion Time (Including	Short Sample (ADLSMP = 0)	D	t _{ADC}	_	20	_	ADCK	See SE8
sample time)	Long Sample (ADLSMP = 1)			_	40	_	cycles	reference manual for
Sample Time	Short Sample (ADLSMP = 0)	D	t _{ADS}	-	3.5	_	ADCK cycles	conversion time variances
	Long Sample (ADLSMP = 1)			1	23.5	1	Cycles	
Temp Sensor	-40°C- 25°C	D	m	1	3.266	1	mV/°C	
Slope	25°C– 125°C	ם	111	1	3.638	1	IIIV/ C	
Temp Sensor Voltage	25°C	D	V _{TEMP25}		1.396		mV	
Characteristics	for 28-pin packages only							
Total	10-bit mode	Р	E _{TUE}	_	±1	±2.5	LSB ³	Includes quantization
Unadjusted Error	8-bit mode	Р		_	±0.5	±1.0		
Differential	10-bit mode ²	Р	DNII	_	±0.5	±1.0	- LSB ³	
Non-Linearity	8-bit mode ³	Р	DNL	_	±0.3	±0.5	LSB	
Integral	10-bit mode	Т	INL	_	±0.5	±1.0	LSB ³	
Non-Linearity	8-bit mode	Т	IINL	_	±0.3	±0.5	LSB	
Zero-Scale	10-bit mode	Р	E .	_	±0.5	±1.5	LSB ³	V _{ADIN} = V _{SSA}
Error	8-bit mode	Р	- E _{ZS}		±0.5	±0.5	LOD	
Full-Scale	10-bit mode	Τ	F	1	±0.5	±1	- LSB ³	$V_{ADIN} = V_{DDA}$
Error	8-bit mode	Т	E _{FS}	_	±0.5	±0.5	LOD	VADIN = VDDA
Quantization	10-bit mode	D	F-	1	_	±0.5	- LSB ³	
Error	8-bit mode	ם	EQ	1	_	±0.5	LOD	
Input Leakage	10-bit mode	D	E _{IL}	_	±0.2	±2.5	- LSB ³	Padleakage ⁴ *
Error	8-bit mode		⊢IL		±0.1	±1	LOD	R _{AS}
Characteristics	for 16-pin package only							
Total	10-bit mode	Р	_	_	±1.5	±3.5	1.053	Includes
Unadjusted Error	8-bit mode	Р	E _{TUE}	_	±0.7	±1.5	LSB ³	quantization



3.10 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

3.10.1 Control Timing

Table 13. Control Timing

Num	С	Rating	Symbol	Min	Typical ¹	Max	Unit
1	D	Bus frequency (t _{cyc} = 1/f _{Bus})	f _{Bus}	DC	_	10	MHz
2	D	Internal low power oscillator period	t _{LPO}	700	_	1300	μs
3	D	External reset pulse width ²	t _{extrst}	100	_	_	ns
4	D	Reset low drive ³	t _{rstdrv}	$34 \times t_{cyc}$	_	_	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t _{MSSU}	500	_	_	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes ⁴	t _{MSH}	100	_	_	μs
7	D	IRQ pulse width Asynchronous path ² Synchronous path ⁵	t _{ILIH,} t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
8	D	Pin interrupt pulse width Asynchronous path ² Synchronous path ⁵	t _{ILIH} , t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
9	С	Port rise and fall time — Low output drive (PTxDS = 0) (load = 50 pF) ⁶ Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t _{Rise} , t _{Fall}	_	40 75	_	ns
9	O	Port rise and fall time — High output drive (PTxDS = 1) (load = 50 pF) Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t _{Rise} , t _{Fall}	_	11 35	_	ns

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

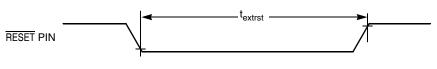


Figure 19. Reset Timing

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² This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

 $^{^{3}}$ When any reset is initiated, internal circuitry drives the reset pin (if enabled, RSTPE = 1) low for about 34 cycles of t_{cyc} .

To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

⁵ This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

 $^{^6}$ Timing is shown with respect to 20% $\rm V_{DD}$ and 80% $\rm V_{DD}$ levels. Temperature range –40 °C to 125 °C.



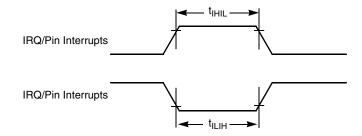


Figure 20. IRQ/Pin Interrupt Timing

3.10.2 TPM/MTIM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Num	С	Rating	Symbol	Min	Max	Unit
1	D	External clock frequency	f _{TPMext}	DC	f _{Bus} /4	MHz
2	D	External clock period	t _{TPMext}	4	_	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5	_	t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	_	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	_	t _{cvc}

Table 14. TPM Input Timing

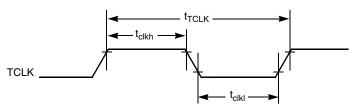


Figure 21. Timer External Clock

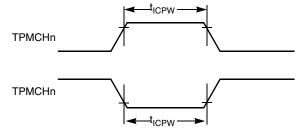
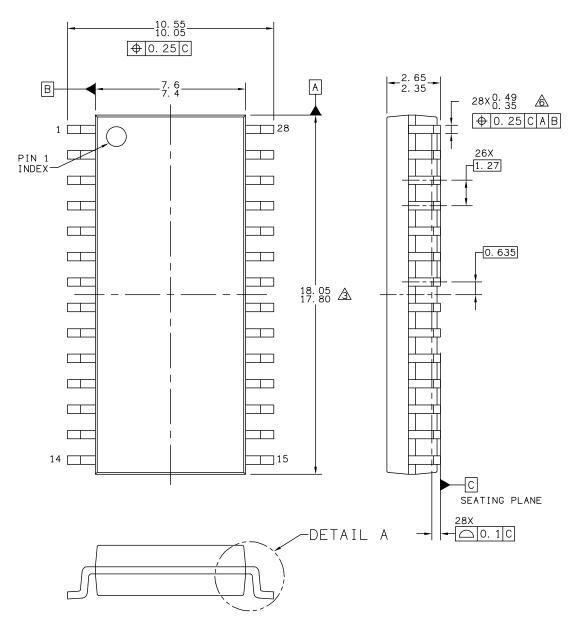


Figure 22. Timer Input Capture Pulse

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28 LEAD	, ,	CASE NUMBER	R: 751F-05	10 MAR 2005
CASEOUTLINE		STANDARD: MS	S-013AE	



NOTES:

- POSITIONAL TOLERANCE OF LEADS, SHALL BE WITHIN 0.25 MM (0.010) AT MAXIMUM MATERIAL CONDITION, IN RELATION TO SEATING PLANE AND EACH OTHER.
- 2. DIMENSION TO CENTER OF LEADS WHEN FORMED PARALLEL.
- A DIMENSION DOES NOT INCLUDE MOLD FLASH.
- 4. 710-01 OBSOLETE, NEW STD 710-02.
- 5. CONTROLLING DIMENSION: INCH

	IN	CH	MILL	_IMETER		INCH		MIL	LIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX	
А	1.435	1.465	36.45	37.21						
В	0.540	0.560	13.72	14.22						
С	0.155	0.200	3.94	5.08						
D	0.014	0.022	0.36	0.56						
F	0.040	0.060	1.02	1.52						
G	0.100	BSC	2.5	34 BSC						
Н	0.065	0.085	1.65	2.16						
J	0.008	0.015	0.20	0.38						
K	0.115	0.135	2.92	3.43						
L	0.600	BSC	15.2	24 BSC						
M	0*	15°	0.	15°						
N	0.020	0.040	0.51	1.02						
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28 LD PDIP					CASE NUMBER: 710-02 24 M			24 MAY 2005		
					STANDARD: NON-JEDEC					

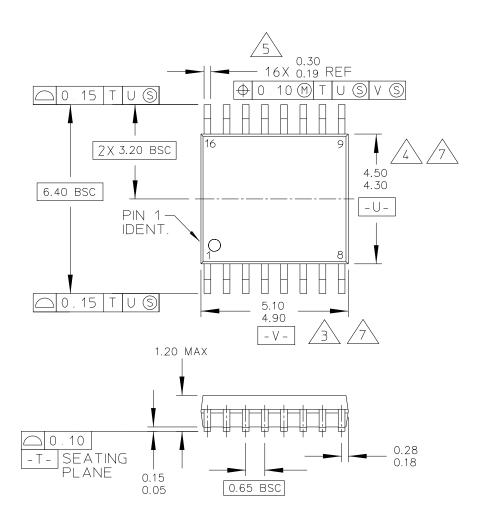
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Ordering Information



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Document Number: MC9S08SE8

Rev. 4 4/2015

